

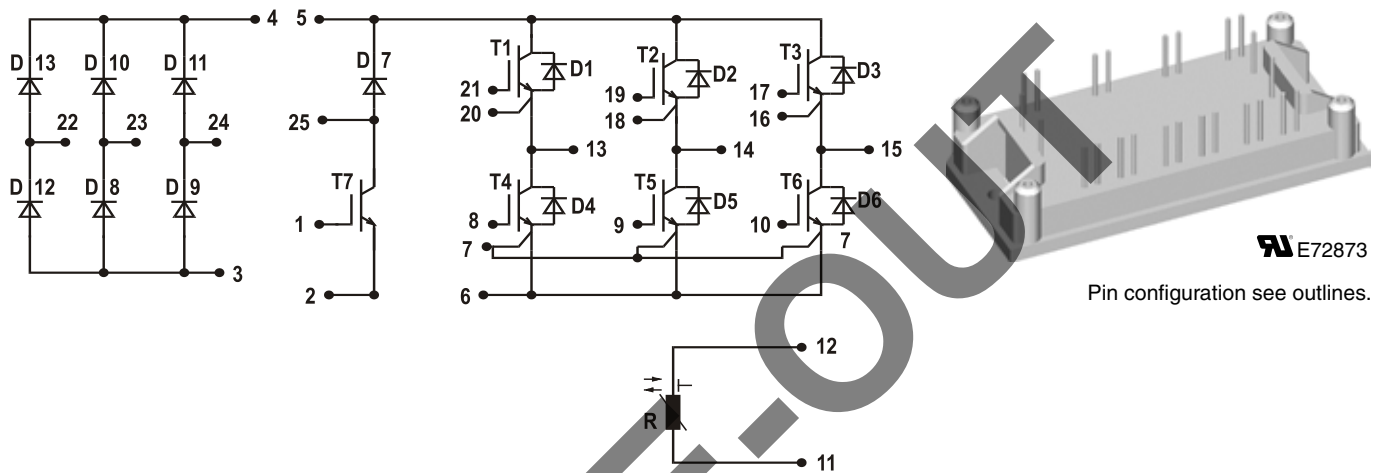
Converter - Brake - Inverter Module (CBI 1) NPT IGBT

Three Phase Rectifier	Brake Chopper	Three Phase Inverter
$V_{RRM} = 1600 \text{ V}$	$V_{CES} = 600 \text{ V}$	$V_{CES} = 600 \text{ V}$
$I_{DAVM25} = 96 \text{ A}$	$I_{C25} = 12 \text{ A}$	$I_{C25} = 19 \text{ A}$
$I_{FSM} = 250 \text{ A}$	$V_{CE(sat)} = 2.25 \text{ V}$	$V_{CE(sat)} = 2.4 \text{ V}$

Preliminary data

Part name (Marking on product)

MUBW15-06A6K



E72873

Pin configuration see outlines.

Features:

- High level of integration - only one power semiconductor module required for the whole drive
- Inverter with NPT IGBTs
- low saturation voltage
- positive temperature coefficient
- fast switching
- short tail current
- Epitaxial free wheeling diodes with hiperfast and soft reverse recovery
- Industry standard package with insulated copper base plate and soldering pins for PCB mounting
- Temperature sense included

Application:

- AC motor drives with
- Input from single or three phase grid
- Three phase synchronous or asynchronous motor
- Electric braking operation

Package:

- UL registered
- Industry standard E1-pack

Output Inverter T1 - T6

Symbol	Definitions	Conditions	Ratings			Unit	
			min.	typ.	max.		
V_{CES}	collector emitter voltage		$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$			V	
V_{GES}	max. DC gate voltage	continuous			± 20	V	
V_{GEM}	max. transient collector gate voltage	transient			± 30	V	
I_{C25}	collector current		$T_C = 25^{\circ}\text{C}$			A	
I_{C80}			$T_C = 80^{\circ}\text{C}$			A	
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$			W	
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 15\text{ A}; V_{GE} = 15\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			2.4	
			$T_{VJ} = 125^{\circ}\text{C}$			2.8	
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 0.35\text{ mA}; V_{GE} = V_{CE}$	$T_{VJ} = 25^{\circ}\text{C}$	4.5		6.5	
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			0.6	
			$T_{VJ} = 125^{\circ}\text{C}$			1.1	
I_{GES}	gate emitter leakage current	$V_{CE} = 0\text{ V}; V_{GE} = \pm 20\text{ V}$				100	
C_{ies}	input capacitance	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}$		600		pF	
$Q_{G(on)}$	total gate charge	$V_{CE} = 300\text{ V}; V_{GE} = 15\text{ V}; I_C = 10\text{ A}$		39		nC	
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 300\text{ V}; I_C = 10\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 82\ \Omega$	$T_{VJ} = 125^{\circ}\text{C}$			40	ns
t_r	current rise time		40	ns			
$t_{d(off)}$	turn-off delay time		230	ns			
t_f	current fall time		30	ns			
E_{on}	turn-on energy per pulse		0.4	mJ			
E_{off}	turn-off energy per pulse		0.3	mJ			
I_{CM}	reverse bias safe operating area	RBSOA; $V_{GE} = \pm 15\text{ V}; R_G = 82\ \Omega$ $L = 100\ \mu\text{H};$ clamped induct. load $V_{CEmax} = V_{CES} - L_S \cdot di/dt$	$T_{VJ} = 125^{\circ}\text{C}$			20	A
t_{SC} (SCSOA)	short circuit safe operating area	$V_{CE} = 600\text{ V}; V_{GE} = \pm 15\text{ V}; R_G = 82\ \Omega;$ non-repetitive	$T_{VJ} = 125^{\circ}\text{C}$			10	μs
R_{thJC}	thermal resistance junction to case	(per IGBT)			1.7	K/W	
R_{thCH}	thermal resistance case to heatsink	(per IGBT)		0.6		K/W	

Output Inverter D1 - D6

Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
V_{RRM}	max. repetitive reverse voltage		$T_{VJ} = 150^{\circ}\text{C}$			600
I_{F25}	forward current		$T_C = 25^{\circ}\text{C}$			21
I_{F80}			$T_C = 80^{\circ}\text{C}$			14
V_F	forward voltage	$I_F = 15\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			2.3
			$T_{VJ} = 125^{\circ}\text{C}$			1.7
I_{RM}	max. reverse recovery current	$V_R = 300\text{ V}$ $di_F/dt = -400\text{ A}/\mu\text{s}$ $I_F = 15\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 100^{\circ}\text{C}$			13
t_{rr}	reverse recovery time		80	ns		
$E_{rec(off)}$	reverse recovery energy		tdb	μJ		
R_{thJC}	thermal resistance junction to case	(per diode)			2.5	K/W
R_{thCH}	thermal resistance case to heatsink	(per diode)		0.85		K/W

 $T_C = 25^{\circ}\text{C}$ unless otherwise stated

Brake Chopper T7

Symbol	Definitions	Conditions	Ratings			Unit	
			min.	typ.	max.		
V_{CES}	collector emitter voltage		$T_{VJ} = 25^{\circ}\text{C}$ to 150°C			V	
V_{GES}	max. DC gate voltage	continuous			± 20	V	
V_{GEM}	max. transient collector gate voltage	transient			± 30	V	
I_{C25}	collector current		$T_C = 25^{\circ}\text{C}$			A	
I_{C80}			$T_C = 80^{\circ}\text{C}$			A	
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$			W	
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 10\text{ A}; V_{GE} = 15\text{ V}$		$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	2.65 3.1	V V	
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 0.2\text{ mA}; V_{GE} = V_{CE}$	4.5	$T_{VJ} = 25^{\circ}\text{C}$		6.5 V	
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$		$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		0.1 mA 0.7 mA	
I_{GES}	gate emitter leakage current	$V_{CE} = 0\text{ V}; V_{GE} = \pm 20\text{ V}$				120 nA	
C_{ies}	input capacitance	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}$			220	pF	
$Q_{G(on)}$	total gate charge	$V_{CE} = 300\text{ V}; V_{GE} = 15\text{ V}; I_C = 6\text{ A}$			32	nC	
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 300\text{ V}; I_C = 8\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 54\ \Omega$ $R_{Goff} = 22\ \Omega$	$T_{VJ} = 125^{\circ}\text{C}$			20	ns
t_r	current rise time					10	ns
$t_{d(off)}$	turn-off delay time					110	ns
t_f	current fall time					30	ns
E_{on}	turn-on energy per pulse					0.21	mJ
E_{off}	turn-off energy per pulse					0.26	mJ
I_{CM}	reverse bias safe operating area	RBSOA; $V_{GE} = \pm 15\text{ V}; R_G = 54\ \Omega$ $L = 100\ \mu\text{H};$ clamped induct. load $V_{CEmax} = V_{CES} - L_S \cdot di/dt$	$T_{VJ} = 125^{\circ}\text{C}$			18	A
t_{SC} (SCSOA)	short circuit safe operating area	$V_{CE} = 600\text{ V}; V_{GE} = \pm 15\text{ V};$ $R_G = 54\ \Omega;$ non-repetitive	$T_{VJ} = 125^{\circ}\text{C}$			10	μs
R_{thJC}	thermal resistance junction to case	(per IGBT)			2.75	K/W	
R_{thCH}	thermal resistance case to heatsink	(per IGBT)			0.9	K/W	

Brake Chopper D7

Symbol	Definitions	Conditions	Ratings			Unit	
			min.	typ.	max.		
V_{RRM}	max. repetitive reverse voltage		$T_{VJ} = 150^{\circ}\text{C}$			V	
I_{F25}	forward current		$T_C = 25^{\circ}\text{C}$			A	
I_{F80}			$T_C = 80^{\circ}\text{C}$			A	
V_F	forward voltage	$I_F = 10\text{ A}; V_{GE} = 0\text{ V}$		$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	2.1 1.25	V V	
I_R	reverse current	$V_R = V_{RRM}$		$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	0.2	0.06 mA mA	
I_{RM}	max. reverse recovery current	$V_R = 100\text{ V}; I_F = 12\text{ A}$ $di_F/dt = -100\text{ A}/\mu\text{s}$	$T_{VJ} = 100^{\circ}\text{C}$			3.5	A
t_{rr}	reverse recovery time					80	ns
R_{thJC}	thermal resistance junction to case	(per diode)			2.5	K/W	
R_{thCH}	thermal resistance case to heatsink	(per diode)			0.85	K/W	

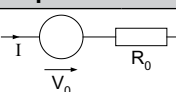
 $T_C = 25^{\circ}\text{C}$ unless otherwise stated

Input Rectifier Bridge D8 - D13					
Symbol	Definitions	Conditions		Maximum Ratings	
V_{RRM}	max. repetitive reverse voltage			1600	V
I_{FAV}	average forward current	sine 180°	$T_C = 80^\circ\text{C}$	23	A
I_{DAVM}	max. average DC output current	rectangular; $d = 1/3$; bridge	$T_C = 80^\circ\text{C}$	65	A
I_{FSM}	max. surge forward current	$t = 10\text{ ms}$; sine 50 Hz	$T_C = 25^\circ\text{C}$	250	A
P_{tot}	total power dissipation	$T_C = 25^\circ\text{C}$		65	W

Symbol	Conditions	Characteristic Values			Unit	
		min.	typ.	max.		
V_F	forward voltage	$I_F = 30\text{ A}$	$T_{VJ} = 25^\circ\text{C}$	1.1	1.45	V
			$T_{VJ} = 125^\circ\text{C}$	1.2		V
I_R	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^\circ\text{C}$	0.4	0.01	mA
			$T_{VJ} = 125^\circ\text{C}$			mA
R_{thJC}	thermal resistance junction to case	(per diode)	$T_{VJ} = 25^\circ\text{C}$		1.9	K/W
R_{thCH}	thermal resistance case to heatsink	(per diode)		0.65		K/W

Temperature Sensor NTC							
Symbol	Definitions	Conditions	Ratings			Unit	
			min.	typ.	max.		
R_{25}	resistance		$T_C = 25^\circ\text{C}$	4.45	4.7	5.0	k Ω
$B_{25/85}$					3510		K

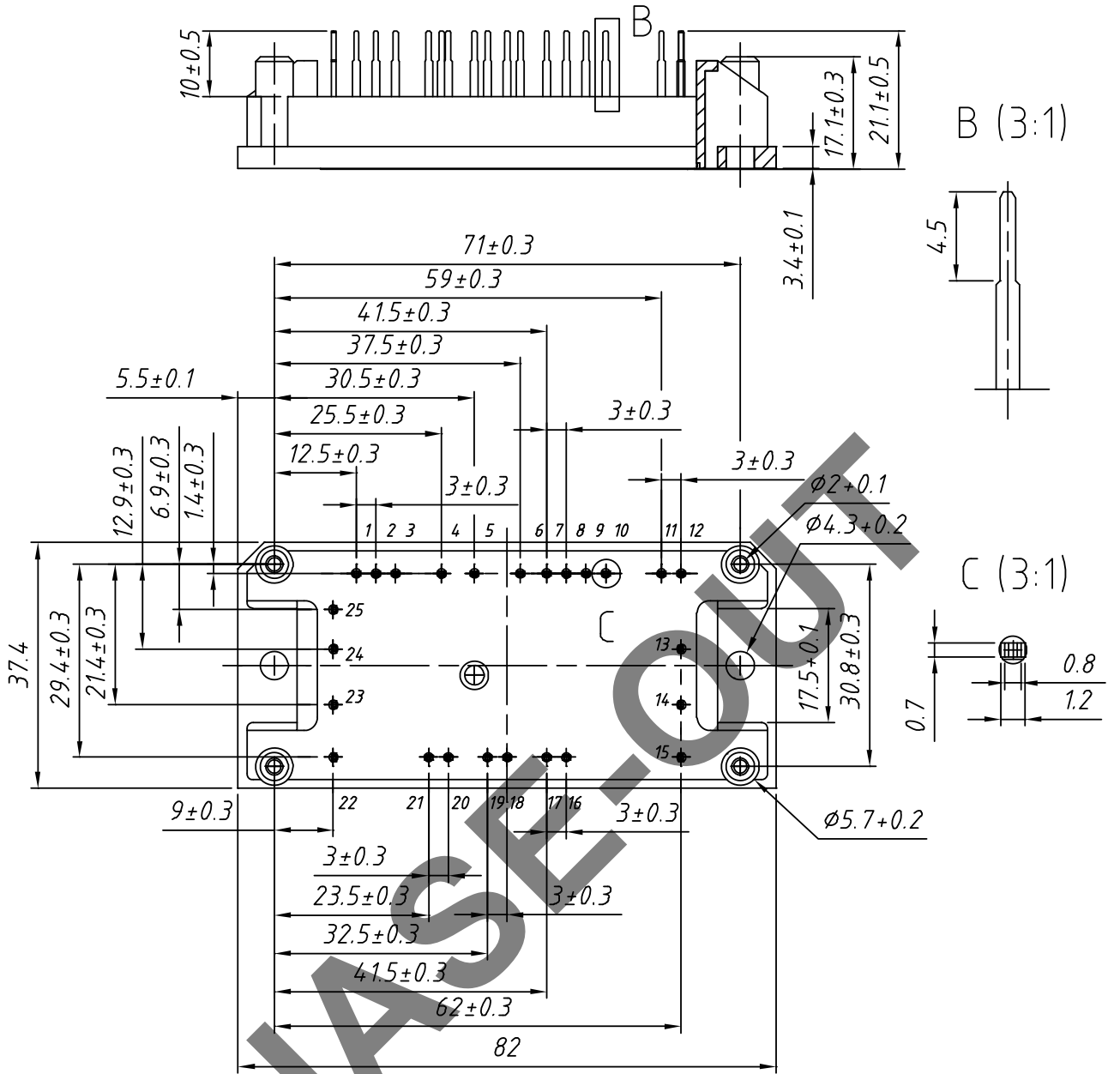
Module						
Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
T_{VJ}	operating temperature		-40		125	$^\circ\text{C}$
T_{VJM}	max. virtual junction temperature				150	$^\circ\text{C}$
T_{stg}	storage temperature		-40		125	$^\circ\text{C}$
V_{ISOL}	isolation voltage	$I_{ISOL} \leq 1\text{ mA}$; 50/60 Hz			2500	V~
M_d	mounting torque	(M4)	2.0		2.2	Nm
d_S	creep distance on surface		12.7			mm
d_A	strike distance through air		12.7			mm
Weight				40		g

Equivalent Circuits for Simulation						
						
Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
V_0	rectifier diode	D8 - D13		0.90		V
R_0				12		m Ω
V_0	IGBT	T1 - T6		1.0		V
R_0				110		m Ω
V_0	free wheeling diode	D1 - D6		1.25		V
R_0				26		m Ω
V_0	IGBT	T7		1.4		V
R_0				150		m Ω
V_0	free wheeling diode	D7		1.25		V
R_0				26		m Ω

 $T_C = 25^\circ\text{C}$ unless otherwise stated

Outline Drawing

Dimensions in mm (1 mm = 0.0394")



Product Marking

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MUBW 15-06A6K	MUBW15-06A6K	Box	10	500 094